### BTA225 series B

### **GENERAL DESCRIPTION**

# Glass passivated high commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

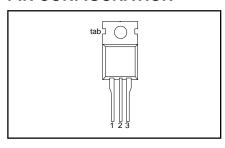
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V <sub>DRM</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BTA225- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	<b>600B</b> 600 25 180	800B 800 25 180	V A A

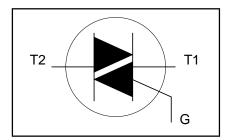
### **PINNING - TO220AB**

PIN	DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
tab	main terminal 2		

### **PIN CONFIGURATION**



### **SYMBOL**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
$V_{DRM}$	Repetitive peak off-state voltages		1	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	\ \
I <sub>T(RMS)</sub>	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 91 ^{\circ}C$ full sine wave; $T_j = 125 ^{\circ}C$ prior to surge; with reapplied $V_{DRM(max)}$	-	25		А
		t = 20 ms t = 16.7 ms	-		30 00	A A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 10.7 ms	-		50 50	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 30 \text{ A}; I_G = 0.2 \text{ A}; \\ dI_G/dt = 0.2 \text{ A}/\mu\text{s}$		100		A/μs
$V_{\rm GM}$	Peak gate current		-	2	2	A
V <sub>GM</sub>	Peak gate voltage		-		5	V W
P <sub>GM</sub>	Peak gate power Average gate power	over any 20 ms period	_		.5	W W
P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	Storage temperature Operating junction temperature	over any 20 ms pendu	-40 -	15	50 25	Ç

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub> R <sub>th j-a</sub>	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	1 1 1	- - 60	1.0 1.4 -	K/W K/W K/W

### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
Gi		T2+ G+	2	18	50	mΑ
		T2+ G-	2	21	50	mΑ
		T2- G-	2 2	34	50	mΑ
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
_		T2+ G+	-	31	60	mΑ
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	31	60	mA
V <sub>T</sub>	On-state voltage	$I_{T} = 30 \text{ A}$	-	1.2	1.55	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.7	1.5	V
	1	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
$I_{D}$	Off-state leakage current	$V_{D} = V_{DRM(max)}$ ; $T_{j} = 125  ^{\circ}C$	-	0.1	0.5	mA

### **DYNAMIC CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/μs
dl <sub>com</sub> /dt	off-state voltage Critical rate of change of	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}$ ; $T_j = 125 \text{ °C}$ ; $I_{T(RMS)} = 25 \text{ A}$ ;	-	44	-	A/ms
t <sub>gt</sub>	commutating current Gate controlled turn-on time	without snubber; gate open circuit $I_{TM} = 30 \text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1 \text{ A}$ ; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

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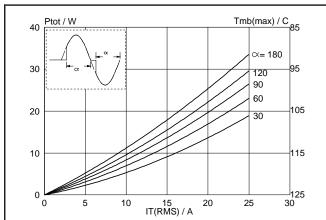


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

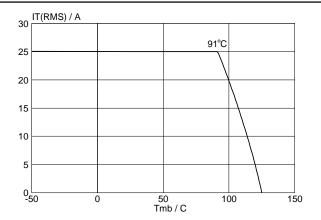


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

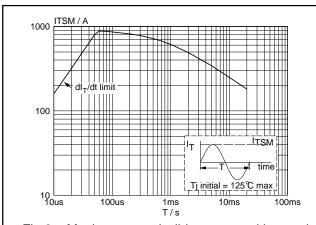


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

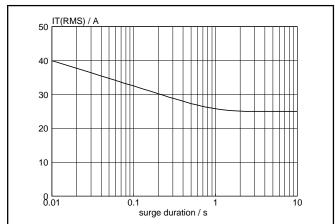


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 91$ °C.

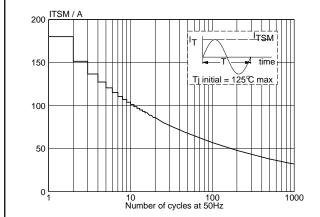


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

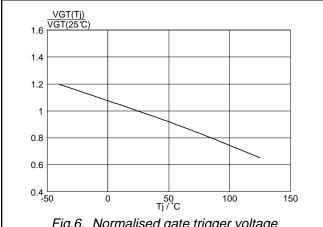
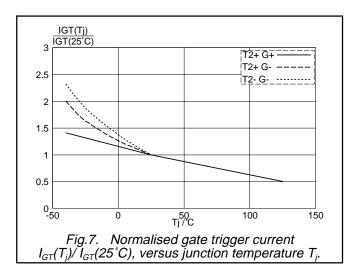
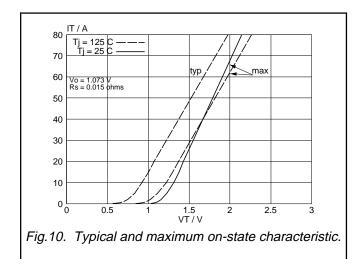
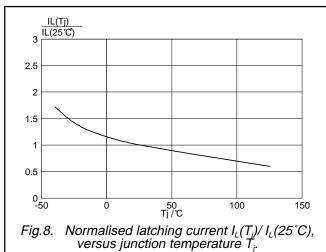


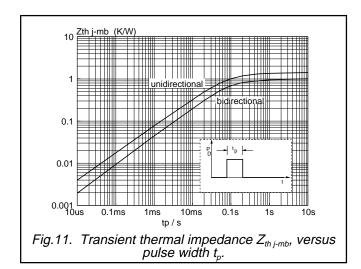
Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25\,^{\circ}C)$ , versus junction temperature  $T_j$ .

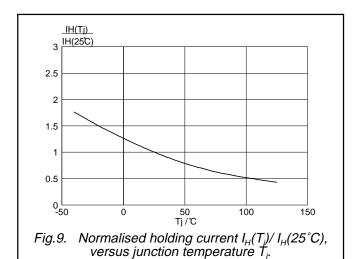
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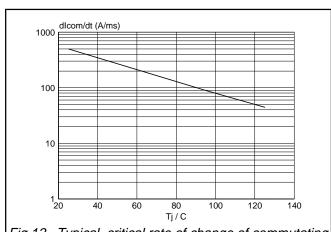
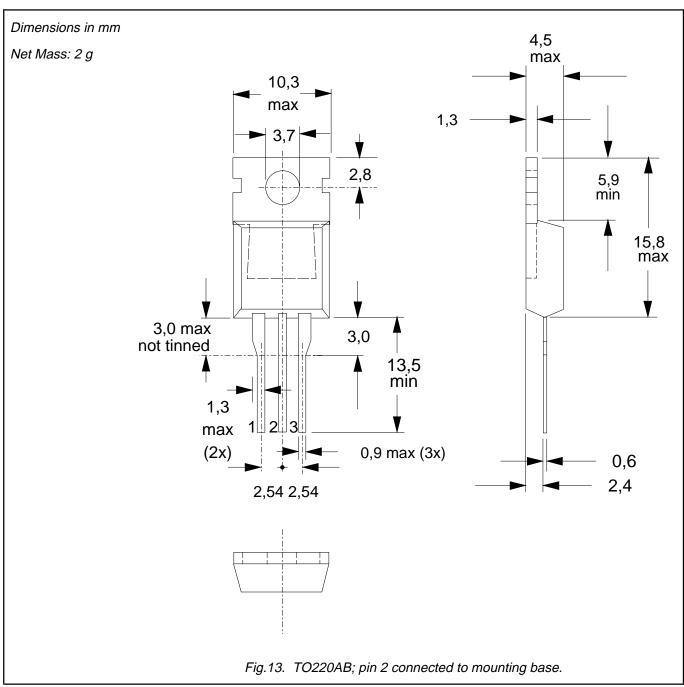


Fig.12. Typical, critical rate of change of commutating current  $dl_{com}/dt$  versus junction temperature.

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### **MECHANICAL DATA**



- Accessories supplied on request: refer to mounting instructions for TO220 envelopes.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

### Triacs high commutation

BTA225 series B

### **DEFINITIONS**

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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